

Supplementary Information for

Perfection of Perovskite Grain Boundary Passivation by Rhodium Incorporation for Efficient and Stable Solar Cells

Wei Liu¹, Nanjing Liu¹, Shilei Ji¹, Hongfeng Hua¹, Yuhui Ma¹, Ruiyuan Hu¹, Jian Zhang¹, Liang Chu^{1,3*}, Xing'ao Li^{1*}, Wei Huang^{1,2,*}

¹Institute of Advanced Materials & New Energy Technology Engineering Laboratory of Jiangsu Province, Nanjing University of Posts and Telecommunications (NUPT), Nanjing 210023, People's Republic of China

²Shaanxi Institute of Flexible Electronics, Northwestern Polytechnical University, Xi'an 710072, People's Republic of China

³Guangdong Provincial Key Lab of Nano-Micro Materials Research, School of Chemical Biology and Biotechnology, Peking University Shenzhen Graduate School, Shenzhen 518055, People's Republic of China

*Corresponding authors. E-mail: chuliang@njupt.edu.cn (Liang Chu), iamxali@njupt.edu.cn (Xing'ao Li), iamwhuang@njupt.edu.cn (Wei Huang)

S1 Characterizations

The morphology of samples was acquired with scanning electron microscopy (SEM, Hitachi S-4800). X-ray diffraction (XRD) patterns were measured with Cu-K α radiation ($\lambda = 1.5418 \text{ \AA}$). Photoluminescence (PL) measurements were used by an Edinburgh F900. Time-resolved PL was measured by a FLS980E fluorometer (Edinburgh Instruments Ltd.), with an excitation wavelength of 785 nm. The UV-vis absorption spectra were recorded using a PerkinElmer Lambda 650S spectrophotometer with the wavelength range from 350 to 800 nm. The X-ray photoemission spectroscopy (XPS) and ultraviolet photoelectron spectroscopy (UPS) were measured using an AXIS Supra. The current density-voltage (J - V) characteristics of the PSCs were acquired by a Keithley 2400 Source under illumination of simulated sunlight (AM 1.5G, 100 mW/cm²) provided by a solar simulator (Newport 91150 USA). Electrochemical impedance spectroscopy (EIS) and Mott-Schottky were measured by CHI660D electrochemical workstation.

Figure S8 shows the $1/C^2$ - V curves of the PSCs for determining the effective hole carrier concentration of the perovskite absorber layer. Using the Mott-Schottky method, the net carrier concentration can be evaluated based on the Equation (Eq. S1) [17]:

$$N_c(W) = \frac{2}{qK_s \varepsilon_0 A^2} \frac{d\left(\frac{1}{C^2}\right)}{dV} \quad (\text{S1})$$

where $N_c(W)$ is the net carrier concentration, q is the electron charge, K_s is the semiconductor dielectric constant, ε_0 is the permittivity of free space, A is the area of the solar cell, C is the capacitance, and V is the applied voltage [17]. It demonstrates that the Rh^{3+} -doped perovskite devices have changed carrier concentration based on above equation, and they also have led to a higher built-in voltage. The higher built-in voltage is favorable for the improvement of open-circuit voltage (V_{oc}), which also accounts for the increase of V_{oc} for Rh^{3+} -doped perovskite device as shown in the measurements.

S2 Supplementary Figures and Tables

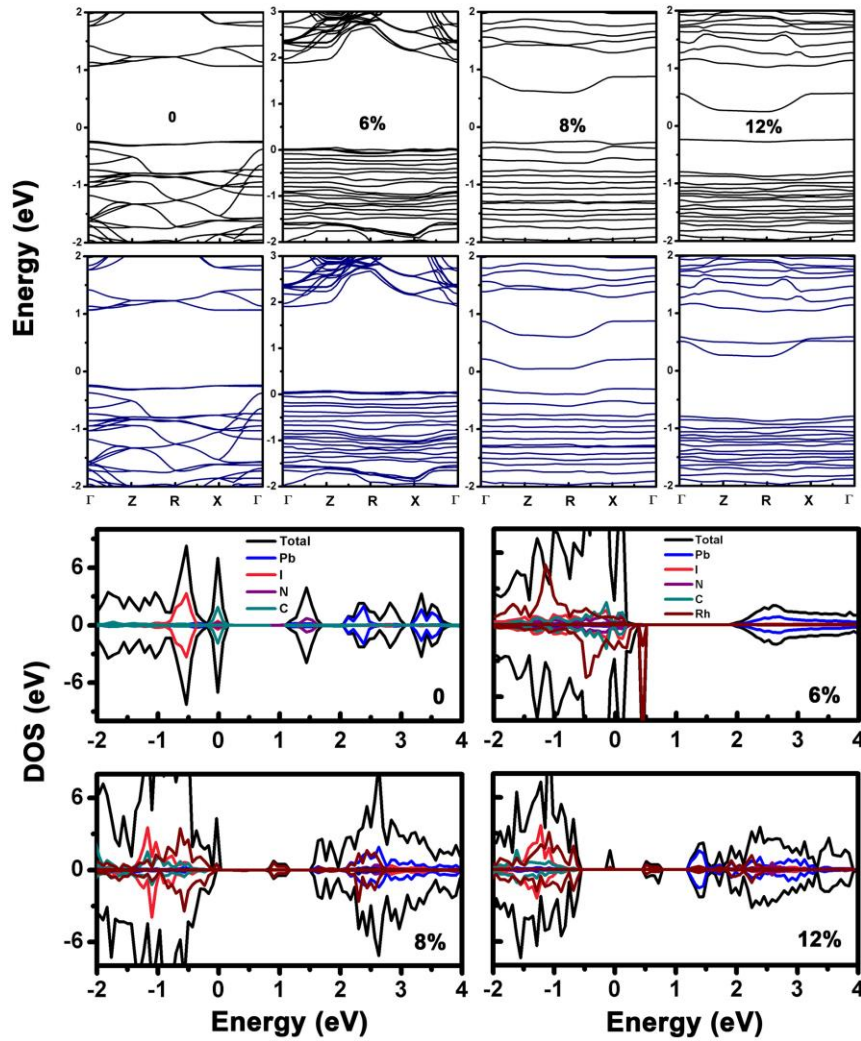


Fig. S1 Band structures, total density of states (DOS) and partial density of states (PDOS) of MAPbI₃:xRh (where x = 0, 6%, 8% and 12%)

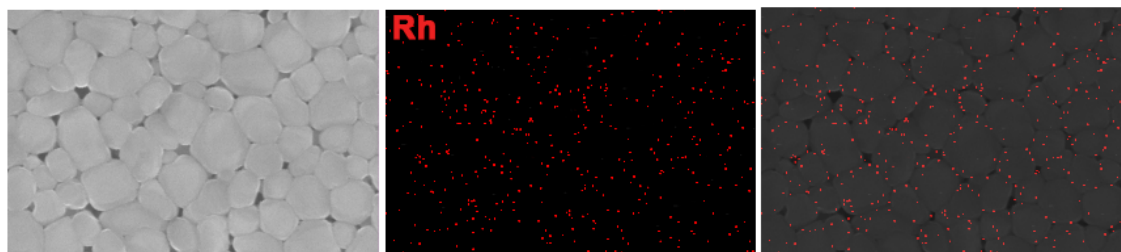


Fig. S2 EELS mapping distribution of $\text{MAPbI}_3:\text{xRh}$ (where $x = 1\%$)

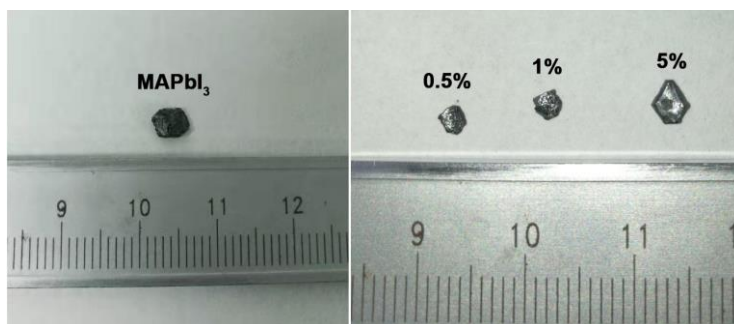


Fig. S3 Photos of the single crystalline perovskite $\text{MAPbI}_3:\text{xRh}$

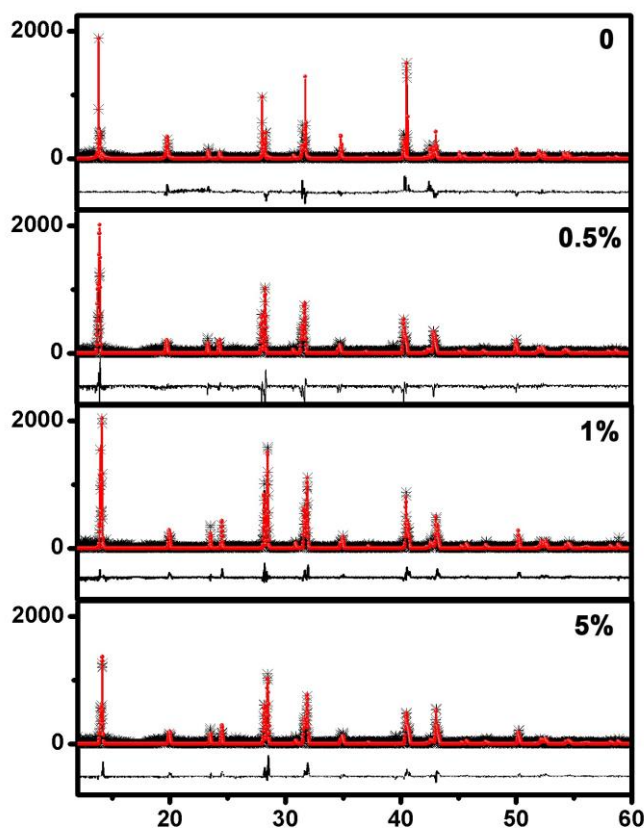


Fig. S4 Rietveld refinement of the XRD patterns of $\text{MAPbI}_3:\text{xRh}$ (where $x = 0, 0.5\%, 1\%$ and 5%). The differences between experiment (red circles) and calculated (black line) spectra are plotted at the bottom

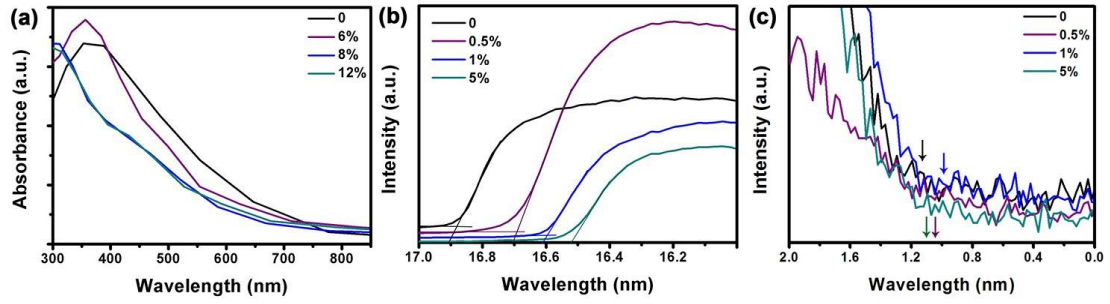


Fig. S5 **a** Absorbance coefficient of calculation results. **b** High binding energy and low binding energy **c** of perovskite films from UPS

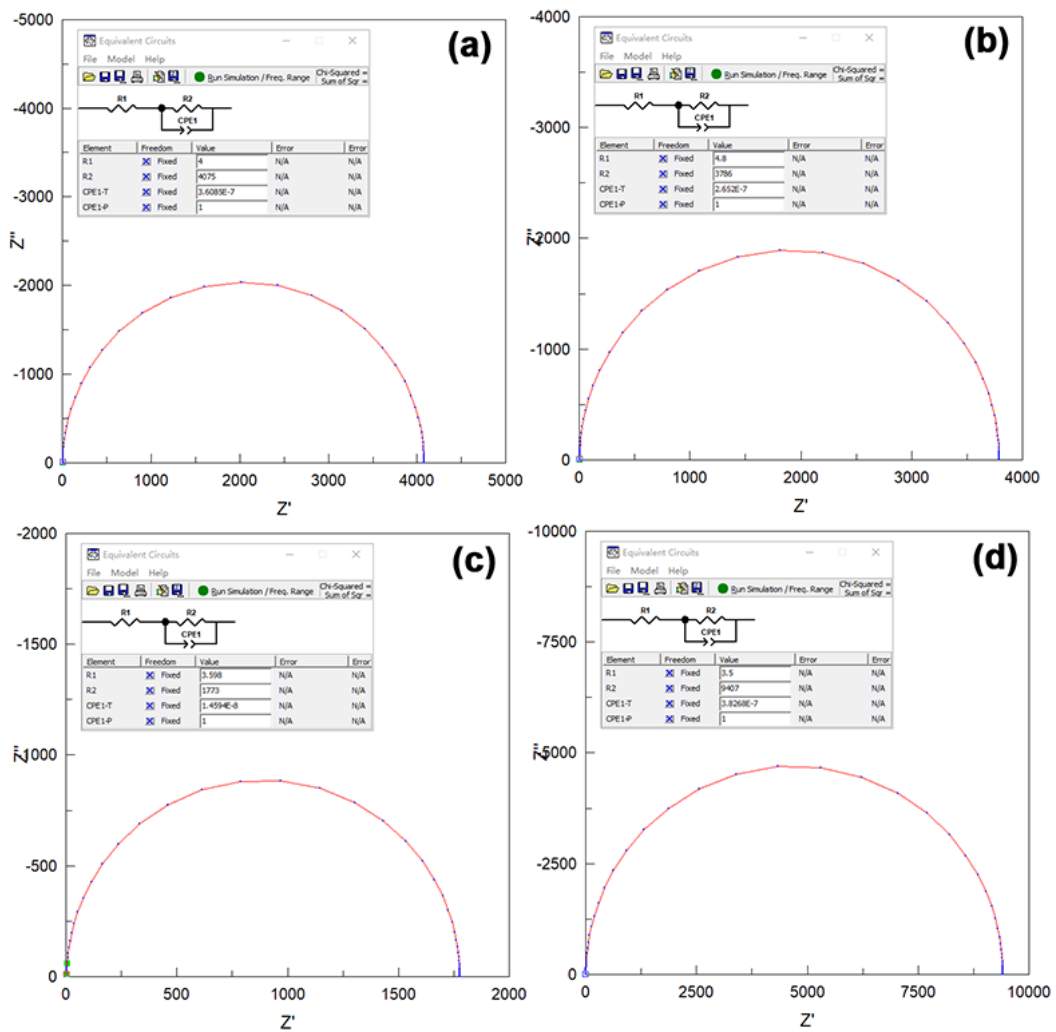


Fig. S6 Data-fitting result of Nyquist plots of PSCs based on MAPbI₃:xRh (where x = 0 **a**, 0.5% **b**, 1% **c**, and 5% **d**)

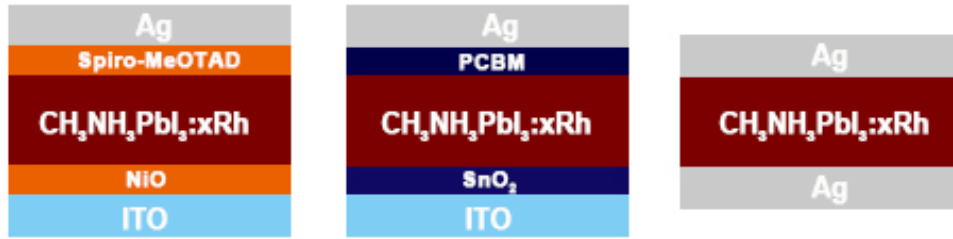


Fig. S7 Device architectures of the hole-only diode and, the electron-only diode perovskite-only device

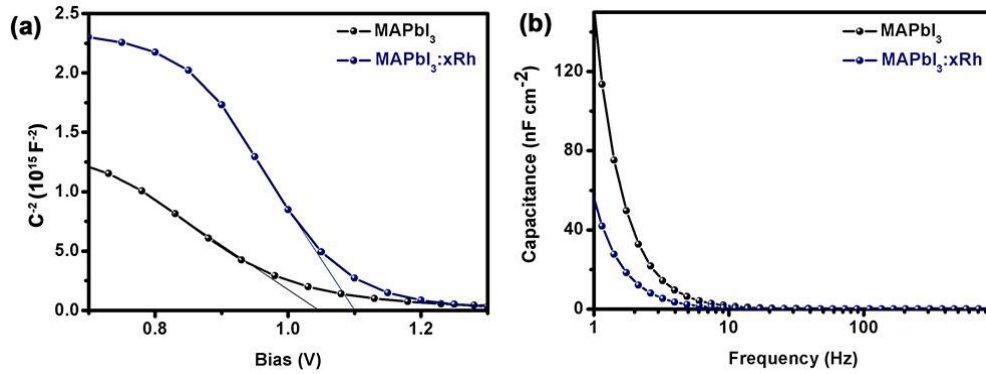


Fig. S8. **a** Mott-Schottky plot obtained from impedance measurements in dark. **b** Frequency-capacitance (F-C) curves measured from perovskite solar cells with and without 1% Rh^{3+} addition

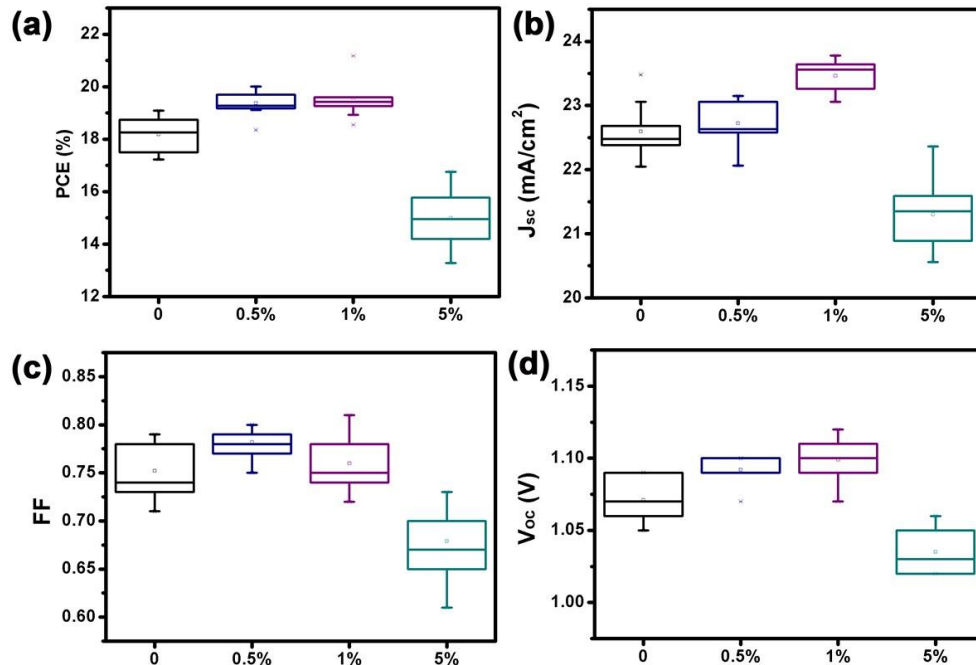


Fig. S9 Statistical photovoltaic parameters of the PSC based on $\text{MAPbI}_3:\text{xRh}$ (where $x = 0, 0.5\%, 1\%,$ and 5%). Photovoltaic parameters of **a** PCE, **b** J_{sc} , **c** FF, and **d** V_{oc} coverage under simulated AM1.5 sunlight of 100 mW cm^{-2} . Each group includes 10 individual devices

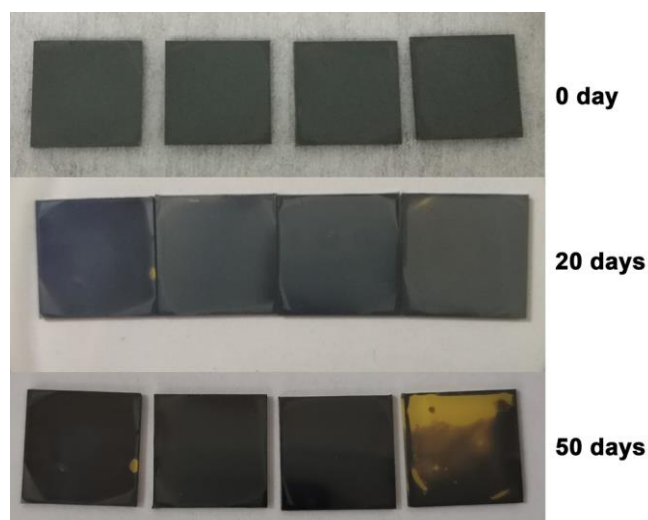


Fig. S10 Perovskite films based on MAPbI_3 and 1% Rh-doped are exposed in the air for 50 days

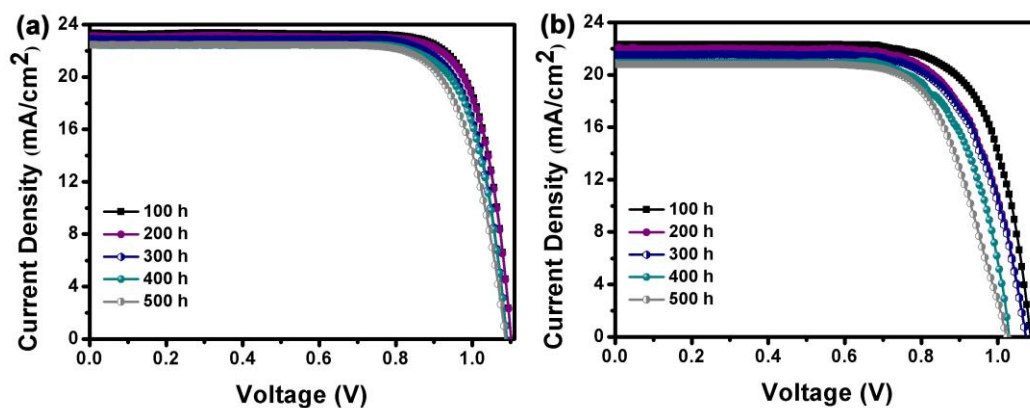


Fig. S11 J-V curves of PSCs based on MAPbI_3 and $\text{MAPbI}_3:\text{xRh}$ with different time at dry air

Table S1 EELS mapping distribution of $\text{MAPbI}_3:\text{xRh}$ (where $x = 1\%$)

Element	Weight%	Atomic%
C	9.11	51.06
N	1.53	7.37
Rh	0.26	0.17
I	60.62	32.15
Pb	28.48	9.25
Totals	100.00	Rh/Pb = 1.8%

Table S2 Selected structural parameters from Rietveld refinement of MAPbI₃:xRh (where x = 0, 0.5%, 1%, and 5%)

Sample	MAPbI ₃	0.5%	1%	5%	calculation
Cell type	I 4 c m	I 4 c m	I 4 c m	I 4 c m	I 4 c m
a	8.86812	8.87288	8.87044	8.86757	8.849
b	8.86812	8.87288	8.87044	8.86757	8.849
c	12.67568	12.68034	12.67468	12.66987	12.642
Cell volume (Å ³)	996.8605035	998.2978011	997.3034668	996.2799945	989.929305
Pb-I bond distance (Å)	3.1538, 3.1689	3.15549, 3.17008	3.15463, 3.16847	3.15360, 3.16747	3.38899, 3.40495
Pb-I-Pb	89.987, 180	89.987, 180	89.987, 180	89.987, 180	
Rp, Rwp	7.55, 9.70	8.84, 11.63	9.13, 11.08	7.53, 9.66	

Table S3 Fermi energy, valence and conduction band from UPS and calculation

Rh-doped	high binding energy	Fermi energy (eV)	low binding energy	valence band (eV)	conduction band (eV)	experiment band gap (eV)	calculate band gap (eV)
0	16.89	-4.33	1.15	-5.48	-3.91	1.57	1.31
0.5%	16.70	-4.52	1.04	-5.56	-3.98	1.58	-
1%	16.60	-4.62	0.92	-5.54	-3.96	1.58	-
5%	16.52	-4.70	1.08	-5.78	-4.19	1.59	1.84

Table S4 Carrier lifetimes of MAPbI₃:xRh (where x = 0, 0.5%, 1%, and 5%) perovskite films

Sample	τ_1/ns	$A_1/\%$	τ_2/ns	$A_2/\%$	$\tau_{\text{avg}}/\text{ns}$
MAPbI ₃	67	0.2715	693	0.7285	671.229
0.5%	72	0.2878	751	0.7122	725.675
1%	63	0.2836	818	0.7164	795.662
5%	55	0.2985	677	0.7015	656.216

Table S5 Photovoltaic performance of PSCs based on MAPbI₃

No.	V_{oc} (V)	J_{sc} (mA/cm ²)	FF	PCE(%)
1	1.09	22.46	0.78	19.09
2	1.07	22.38	0.78	18.67
3	1.09	22.26	0.72	17.47
4	1.05	23.48	0.71	17.50
5	1.07	22.54	0.73	17.60
6	1.09	22.05	0.78	18.74
7	1.06	22.58	0.79	18.91
8	1.07	23.06	0.74	18.26
9	1.07	22.68	0.76	18.44
10	1.05	22.48	0.73	17.23
Average	1.07±0.02	22.60±0.8	0.75±0.04	18.19±0.96

Table S6 Photovoltaic performance of PSCs based on MAPbI₃:xRh (where x = 0.5%)

No.	V_{oc} (V)	J_{sc} (mA/cm ²)	FF	PCE(%)
1	1.09	23.13	0.79	20.01
2	1.10	22.06	0.80	19.41
3	1.09	22.58	0.78	19.20
4	1.09	23.06	0.79	19.86
5	1.09	22.68	0.80	19.70
6	1.07	23.15	0.79	19.64
7	1.10	22.59	0.78	19.28
8	1.09	22.45	0.75	18.35
9	1.10	22.89	0.77	19.17
10	1.10	22.63	0.77	19.12
Average	1.08±0.02	22.72±0.43	0.78±0.03	19.37±1.02

Table S7 Photovoltaic performance of PSCs based on MAPbI₃:xRh (where x = 1%)

No.	V_{oc} (V)	J_{sc} (mA/cm ²)	FF	PCE(%)
1	1.10	23.82	0.79	20.71
2	1.11	23.56	0.75	19.60
3	1.11	23.68	0.75	19.59
4	1.12	23.58	0.74	19.45
5	1.07	23.06	0.78	19.26
6	1.07	23.26	0.78	19.43
7	1.09	23.58	0.79	20.27
8	1.11	23.64	0.74	19.35
9	1.10	23.38	0.72	18.55
10	1.11	23.14	0.74	18.93
Average	1.10±0.03	23.47±0.41	0.76±0.05	19.51±1.2

Table S8 Photovoltaic performance of PSCs based on MAPbI₃:xRh (where x = 5%)

No.	V_{oc} (V)	J_{sc} (mA/cm ²)	FF	PCE(%)
1	1.06	21.44	0.73	16.76
2	1.02	21.35	0.61	13.28
3	1.04	20.56	0.65	13.90
4	1.03	21.68	0.67	14.96
5	1.03	20.89	0.67	14.42
6	1.05	21.47	0.63	14.20
7	1.05	20.58	0.73	15.77
8	1.03	21.06	0.70	15.18
9	1.02	21.59	0.70	15.41
10	1.02	22.36	0.70	15.96
Average	1.03±0.03	21.30±1.06	0.67±0.06	14.98±1.78

Table S9 Photocurrent hysteresis studies of the PSCs fabricated by pristine MAPbI₃ thin film and the MAPbI₃:xRh (x = 1 mol%) thin film

Devices		V_{oc} (V)	J_{sc} (mA/cm ²)	FF	PCE(%)	HI
MAPbI ₃	Reverse	1.09	22.46	0.78	19.09	0.042
	Forward	1.09	21.76	0.77	18.26	
1% Rh	Reverse	1.10	23.82	0.79	20.71	0.020
	Forward	1.09	23.87	0.78	20.29	

Table S10 The hole and electron mobilities and the defect densities of pristine MAPbI₃ thin film and the MAPbI₃:xRh (x = 1%) thin film

Hybrid perovskite materials	Hole mobility (cm ² V ⁻¹ s ⁻¹)	Electron mobility (cm ² V ⁻¹ s ⁻¹)	Hole defects (cm ⁻³)	Electron defects (cm ⁻³)
MAPbI ₃	1.29×10 ⁻³	5.38×10 ⁻³	3.10×10 ¹⁵	2.74×10 ¹⁶
MAPbI ₃ :xRh (x = 1%)	2.51×10 ⁻²	1.26×10 ⁻²	8.09×10 ¹⁵	1.26×10 ¹⁵

Table S11 Summary of the device performance data for PSCs based on different light absorbers and doping

Absorber	Doping	PCE(%)	Year	Refs.
MAPbI ₃	Al ³⁺	19.1%	2016	S1
MAPbI ₃	Li ⁺	18.1%	2017	S2
MAPbI ₃	Ag ⁺	20.02%	2018	S3
MAPbI ₃	Zn ²⁺	18.35%	2018	S4
MAPbI ₃	Ni ²⁺	20.63%	2018	S5
MAPbI ₃	Mn ²⁺	19.09%	2019	S6
MAPbI ₃	R ³⁺	20.71%	-	This work
MAPbI ₃	Nd ³⁺	21.15%	2019	S7
MAPb _{0.85} In _{0.15} I ₃ Cl _{0.15}	In ³⁺	17.55%	2016	S8
MAPbI _{3-x} Cl _x	Ca ²⁺	12.0%	2017	S9
MAPbI _{3-x} Cl _x	Sr ²⁺	11.2%	2017	S9
MAPbI _{3-x} Cl _x	Ba ²⁺	14.9%	2017	S9
MASr _a Pb _{1-a} I _{3-x} Cl _x	Sr ²⁺	16.3%	2017	S10
MAPb _{0.9} Co _{0.1} I ₃	Co ²⁺	21.43%	2018	S11
MAPb _{0.9} Sn _{0.05} Cu _{0.05} I _{2.9} B r _{0.1}	Cu ²⁺	21.08%	2018	S12
MAPb _x Mg _{1-x} I _{3-y} Cl _y	Mg ²⁺	14.2%	2018	S13
MA _{1-x} K _x PbI ₃	K ⁺	11.05%	2019	S14
FA _x MA _{1-x} PbI ₃	Eu ³⁺	21.52%	2019	S15
(FA) _{0.83} (MA) _{0.17} PbI _{0.83} Br 0.17	Gd ³⁺	21.21%	2020	S16

Table S12 Performance of PSCs based on MAPbI₃ and MAPbI₃:xRh with different time at dry air

No.	V_{oc} (V)	J_{sc} (mA cm ⁻²)	FF	PCE(%)
MAPbI ₃ -100h	1.09	22.31	0.76	18.48
MAPbI ₃ -200h	1.07	21.94	0.71	16.67
MAPbI ₃ -300h	1.07	21.51	0.71	16.34
MAPbI ₃ -400h	1.03	20.91	0.71	15.29
MAPbI ₃ -500h	1.03	20.46	0.68	14.06
MAPbI ₃ :xRh-100h	1.10	23.36	0.79	20.30
MAPbI ₃ :xRh-200h	1.09	23.12	0.79	19.91
MAPbI ₃ :xRh-300h	1.09	22.92	0.78	19.49
MAPbI ₃ :xRh-400h	1.09	22.52	0.78	19.15
MAPbI ₃ :xRh-500h	1.08	22.45	0.77	19.04

Supplementary References

- [S1] J.W. Wang, Z. Wang, S. Pathak, W. Zhang, D. W. deQuilettes, et al., Efficient perovskite solar cells by metal ion doping. *Energy Environ. Sci.* **9**(9), 2892-2901 (2016). <https://doi.org/10.1039/C6EE01969B>
- [S2] J. Zhang, R. Chen, Y. Wu, M. Shang, Z. Zeng, Y. Zhang, Y. Zhu, L. Han, Extrinsic movable ions in MAPbI₃ modulate energy band alignment in perovskite solar cells. *Adv. Energy Mater.* **8**(5), 1701981 (2018). <https://doi.org/10.1002/aenm.201701981>
- [S3] Y. Zhang, C.C. Zhang, C.H. Gao, M. Li, X. J. Ma, et al., N-type doping of organic-inorganic hybrid perovskites toward high-performance photovoltaic devices. *Solar RRL* **3**(2), 1800269 (2019). <https://doi.org/10.1002/solr.201800269>
- [S4] H. Zheng, G. Liu, X. Xu, A. Alsaedi, T. Hayat, X. Pan, S. Dai, Acquiring High-Performance and Stable Mixed-Dimensional Perovskite Solar Cells by Using Transition Metal Substituted Pb. *ChemSusChem* **11**, 3269-3275 (2018). <https://doi.org/10.1002/cssc.201801171>
- [S5] X. Gong, L. Guan, H. Pan, Q. Sun, X. Zhao, et al., Highly efficient perovskite solar cells via nickel passivation. *Adv. Funct. Mater.* **28**(50), 1804286 (2018). <https://doi.org/10.1002/adfm.201804286>
- [S6] W. Liu, L. Chu, N. Liu, Y. Ma, R. Hu, et al., Efficient perovskite solar cells fabricated by manganese cations incorporated in hybrid perovskites. *J. Mater.*

- Chem. C **7**(38), 11943-11952 (2019). <https://doi.org/10.1039/C9TC03375K>
- [S7] K. Wang, L. Zheng, T. Zhu, X. Yao, C. Yi, et al., Efficient perovskite solar cells by hybrid perovskites incorporated with heterovalent neodymium cations. *Nano Energy* **61**, 352-360 (2019). <https://doi.org/10.1016/j.nanoen.2019.04.073>
- [S8] Z. K. Wang, M. Li, Y. G. Yang, Y. Hu, H. Ma, et al., High efficiency Pb-In binary metal perovskite solar cells. *Adv. Mater.* **28**(31), 6695-6703 (2016). <https://doi.org/10.1002/adma.201600626>
- [S9] S.H. Chan, M.C. Wu, K.M. Lee, W.C. Chen, T.H. Lin, W.F. Su, Enhancing perovskite solar cell performance and stability by doping barium in methylammonium lead halide. *J. Mater. Chem. A* **5**, 18044-18052 (2017). <https://doi.org/10.1039/C7TA05720B>
- [S10] X. Shai, L. Zuo, P. Sun, P. Liao, W. Huang et al., Efficient planar perovskite solar cells using halide Sr-substituted Pb perovskite. *Nano Energy* **36**, 213-222 (2017). <https://doi.org/10.1016/j.nanoen.2017.04.047>
- [S11] W. Xu, L. Zheng, X. Zhang, Y. Cao, T. Meng et al., Efficient perovskite solar cells fabricated by Co partially substituted hybrid perovskite. *Adv. Energy Mater.* **8**(14), 1703178 (2018). <https://doi.org/10.1002/aenm.201703178>
- [S12] M. Li, Z.K. Wang, M.P. Zhuo, Y. Hu, K.H. Hu et al., Pb-Sn-Cu ternary organometallic halide perovskite solar cells. *Adv. Mater.* **30**, 1800258 (2018). <https://doi.org/10.1002/adma.201800258>
- [S13] P. Singh, P. J. S. Rana, R. Mukherjee, P. Srivastava, A step towards environmental benign Mg/Pb based binary metal mixed halide perovskite material. *Sol. Energy* **170**, 769-779 (2018). <https://doi.org/10.1016/j.solener.2018.05.090>
- [S14] Y. Yao, X. Zou, J. Cheng, T. Ling, C. Chang, D. Chen, Impact of K⁺ doping on modulating majority charge carrier type and quality of perovskite thin films by two-step solution method for solar cells. *Coatings* **9**, 647 (2019). <https://doi.org/10.3390/coatings9100647>
- [S15] L. Wang, H. Zhou, J. Hu, B. Huang, M. Sun, et al., A Eu³⁺-Eu²⁺ ion redox shuttle imparts operational durability to Pb-I perovskite solar cells. *Science* **363**(6424), 265-270 (2019). <https://doi.org/10.1126/science.aau5701>
- [S16] Y. Yang, J. Wu, X. Wang, Q. Guo, X. Liu et al., Suppressing vacancy defects and grain boundaries via ostwald ripening for high-performance and stable perovskite solar cells. *Adv. Mater.* 1904347 (2019). <https://doi.org/10.1002/adma.201904347>
- [S17] W. Zhao, Z. Yao, F. Yu, D. Yang, S.F. Liu, Alkali metal doping for improved CH₃NH₃PbI₃ perovskite solar cells. *Adv. Sci.* **5**(2), 1700131 (2018). <https://doi.org/10.1002/advs.201700131>